

RJP5001APP

Nch IGBT for Strobe Flash

REJ03G1710-0100 Rev.1.00 Jul 03, 2008

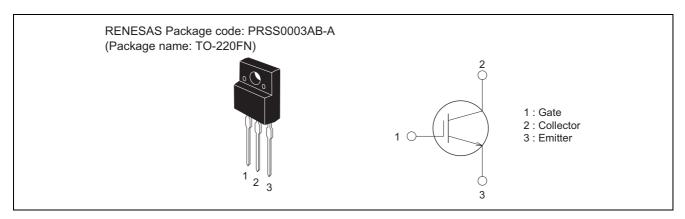
Features

• V_{CES}: 500 V

• TO-220FN package

• High Speed Switching

Outline



Applications

Strobe flash

www.

Maximum Ratings

 $(Tc = 25^{\circ}C)$

DataSheet4U. Parameter	Symbol	Ratings	Unit	Conditions
Collector-emitter voltage	V _{CES}	500	V	V _{GE} = 0 V
Gate-emitter voltage	V _{GES}	±17	V	V _{CE} = 0 V, Refer to item 4 under Notes on the Actual Specifications
Collector current (Pulse)	I _{CM}	300	A	$C_M = 2000 \mu\text{F}$ (see performance curve)
Maximum power dissipation	Pc	45	W	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	_	2.0	g	Typical value

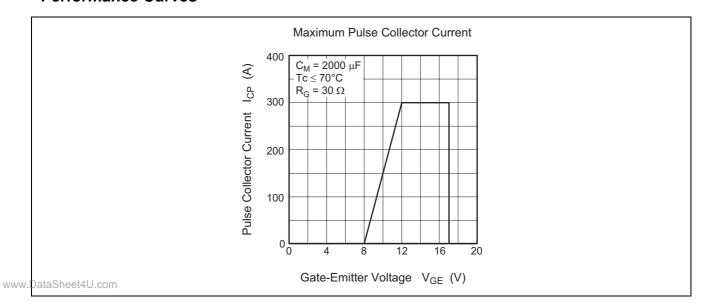
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Electrical Characteristics

 $(Tj = 25^{\circ}C)$

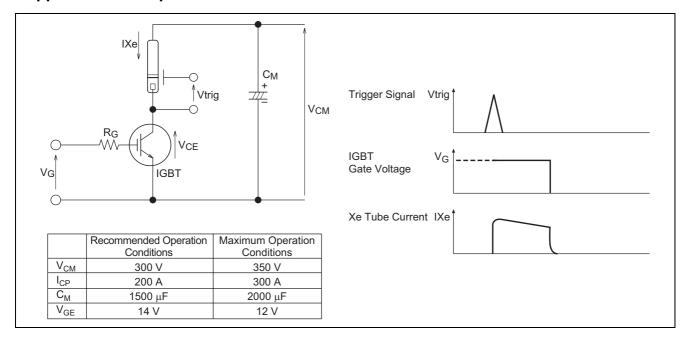
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
Collector-emitter breakdown voltage	$V_{(BR)CES}$	500	_	_	V	$I_C = 100 \mu\text{A}, V_{GE} = 0 \text{V}$
Collector-emitter leakage current	I _{CES}	_	_	10	μΑ	$V_{CE} = 500 \text{ V}, V_{GE} = 0 \text{ V}$
Gate-emitter leakage current	I _{GES}	_	_	±0.1	μΑ	$V_{GE} = \pm 17 \text{ V}, V_{CE} = 0 \text{ V}$
Gate-emitter threshold voltage	$V_{GE(th)}$	1.3	_	2.7	V	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$
Collector-emitter saturation voltage	V _{CE(sat)}	_	4.7	10	V	I _C = 300 A, V _{GE} = 12 V
Input capacitance	Ciss	_	2050	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	130	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	12	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	0.1	_	μs	V _{DD} = 300 V
Rise time	t _r	_	0.5	_	μs	I _D = 12 A
Turn-off delay time	t _{d(off)}	_	0.2	_	μs	$V_{GS} = 350 \text{ V}$
Fall time	t _f	_	0.8	_	μs	$R_G = 25 \Omega$

Performance Curves



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Application Example



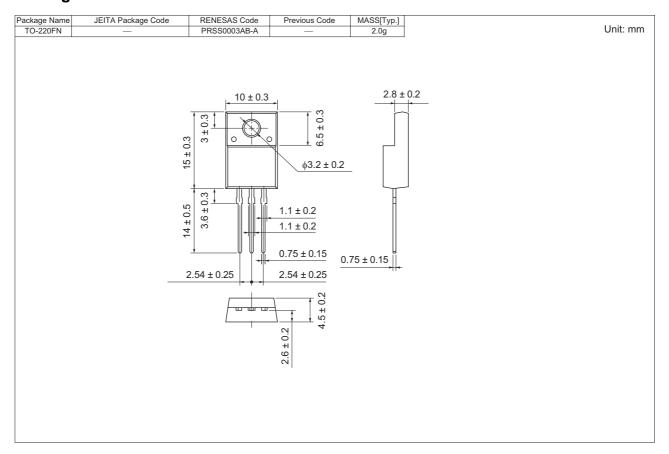
Precautions on Usage

- 1. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current. And turn-off dv/dt must become less than $1000~V/\mu s$.
- 2. IGBT has MOS structure and its gate is insulated by thin silicon oxide. So please handle carefully to protect the device from electrostatic charge.
- 3. The operation life should be endured until repeated discharge of 5,000 times under the charge current ($I_{Xe} \le 300 \text{ A}$: full luminescence condition) of main capacitor. Repetition period under full luminescence condition is over 5 seconds
- 4. Total operation hours applied to the gate-emitter voltage must be within 5,000 hours.

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Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container		
RJP5001APP-00-T2	50 pcs	Magazine (Tube)		

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Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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Renesas Technology America, Inc.

www.DataSl h4504holgemWay, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510